

N-channel 60 V, 0.0024 Ω , 120 A STripFET™ VI DeepGATE™ Power MOSFET in TO-220 and I²PAK packages

Features

Order codes	V _{DSS}	R _{DS(on)} max	I _D
STI260N6F6	60 V	< 0.003 Ω	120 A
STP260N6F6			

- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

Application

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFETs exhibits the lowest R_{DS(on)} in all packages.

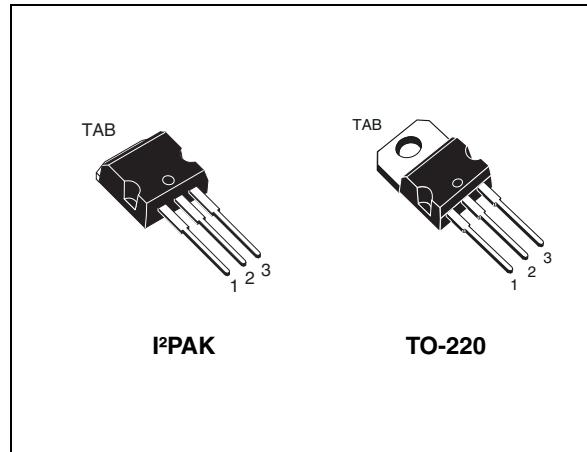


Figure 1. Internal schematic diagram

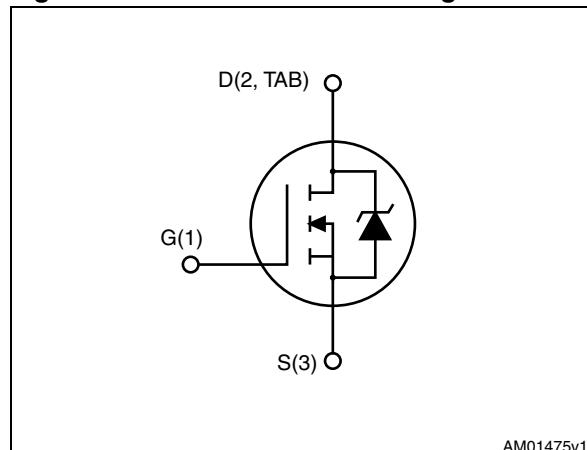


Table 1. Device summary

Order codes	Marking	Package	Packaging
STI260N6F6	260N6F6	I ² PAK	Tube
STP260N6F6		TO-220	

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	120	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	120	A
$I_{DM}^{(1)}$	Drain current (pulsed)	480	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Current limited by package.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_I	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25^\circ\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250 \mu\text{A}$	60			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = 60 \text{ V}$ $V_{DS} = 60 \text{ V}, T_C = 125^\circ\text{C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 100	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2		4	V
$R_{DS(\text{on})}$	Static drain-source on-resistance	$V_{GS} = 10 \text{ V}, I_D = 60 \text{ A}$		2.4	3	$\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			11400		pF
C_{oss}	Output capacitance	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$	-	850	-	pF
C_{rss}	Reverse transfer capacitance			368		pF
Q_g	Total gate charge	$V_{DD} = 30 \text{ V}, I_D = 120 \text{ A}, V_{GS} = 10 \text{ V}$		183		nC
Q_{gs}	Gate-source charge		-	53	-	nC
Q_{gd}	Gate-drain charge			41		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(\text{on})}$	Turn-on delay time	$V_{DD} = 30 \text{ V}, I_D = 60 \text{ A}$ $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$	-	31.4	-	ns
t_r	Rise time			165	-	ns
$t_{d(\text{off})}$	Turn-off-delay time		-	144.4	-	ns
t_f	Fall time			62.6	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120 \text{ A}, V_{GS} = 0$	-		1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 120 \text{ A}, V_{DD} = 48 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s},$ $T_j = 150^\circ\text{C}$	-	55.6 116 3.8		ns nC A

1. Current limited by package.
 2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

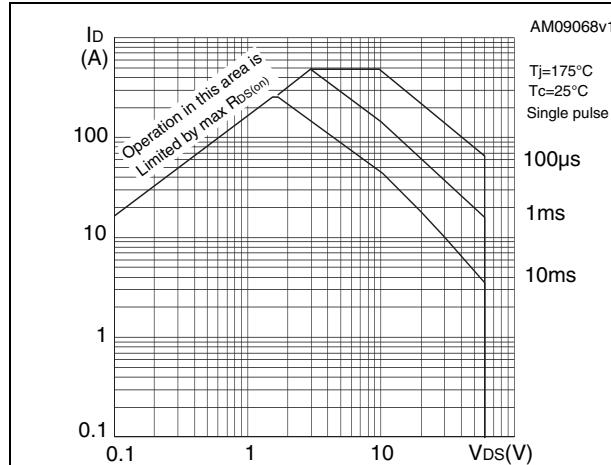


Figure 3. Thermal impedance

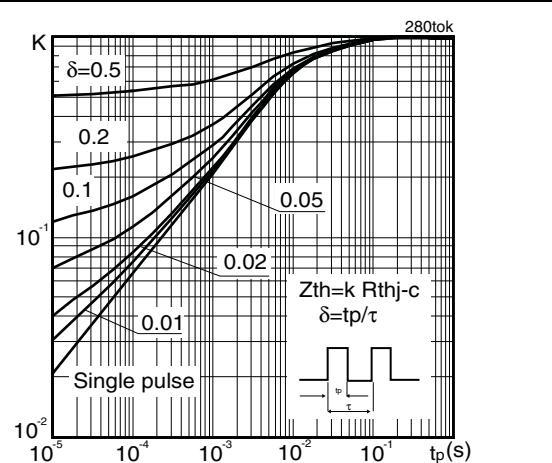


Figure 4. Output characteristics

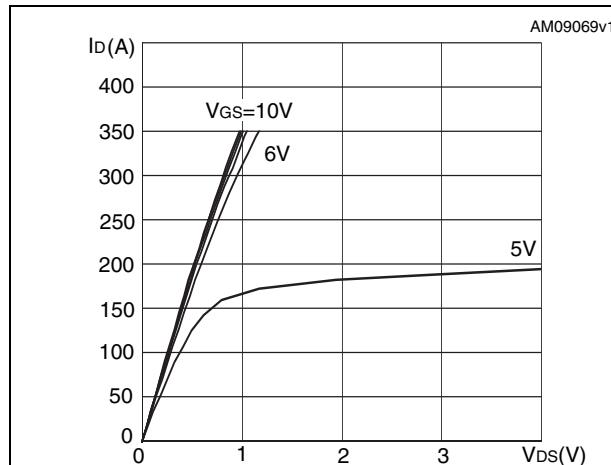


Figure 5. Transfer characteristics

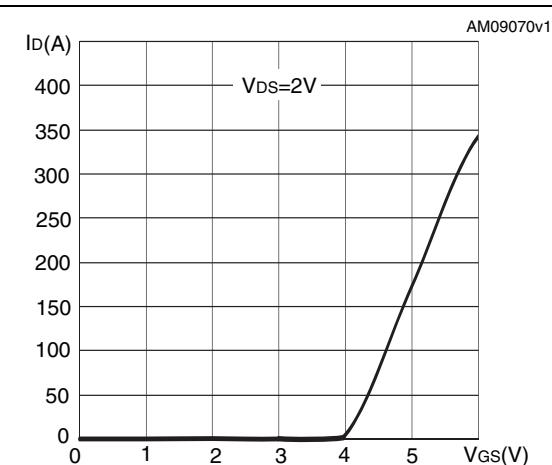
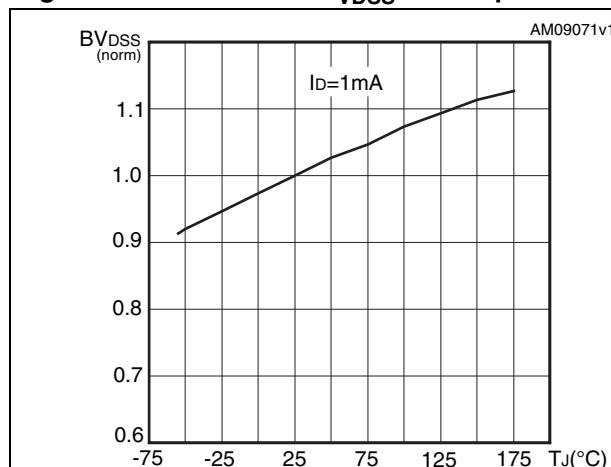
Figure 6. Normalized B_{VDSS} vs. temperature

Figure 7. Static drain-source on resistance

